

Features

- Freq: 2~18GHz
- Isolation: 14dB
- Insertion Loss: 0.8dB
- Chip Size: 1.3mm×0.65mm×0.1mm

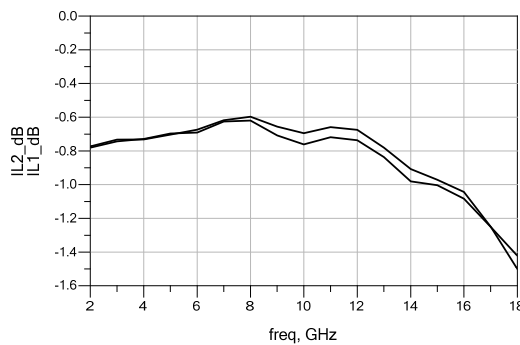
General Description

The HG126G is a 2-way GaAs pHEMT power divider that is operating from 2 to 18 GHz. This chip features very high isolation of 16 dB and extremely low insertion loss of 0.8dB. Input and Output VSWR are 1.4/1.4.

Electrical Specifications (T_A=25 °C)

| Parameter | Min. | Typ. | Max. |
|----------------------|------|------|------|
| Frequency Range(GHz) | 2~18 | | |
| Input VSWR | - | 1.4 | - |
| Output VSWR | - | 1.4 | - |
| Insertion Loss(dB) | - | 0.8 | - |
| Isolation (dB) | - | 14 | - |

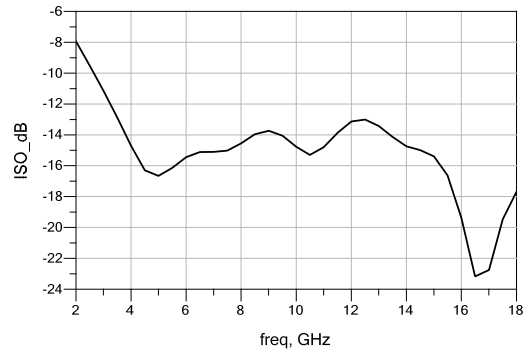
Insertion Loss



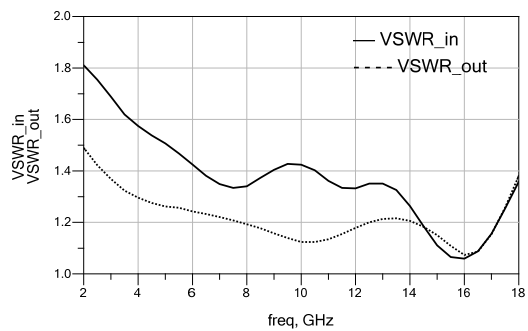
Absolute Maximum Ratings

| | |
|-----------------------|-------------|
| RF Input Power | +27dBm |
| Operating Temperature | -55°C~125°C |
| Storage Temperature | -65°C~150°C |

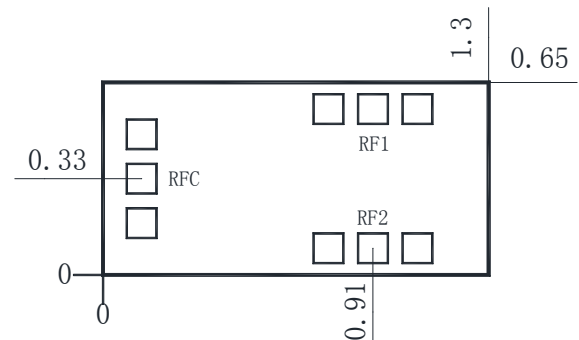
Isolation



Input and Output VSWR



Outline Drawing (mm)



Notes:

- The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
- GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
- The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300°C, and no more than 30 sec.), and should make it fully grounded.
- The chip microwave port and substrate gap is not exceeding 0.05mm, with Φ25μm double gold wire bonding, suggested length of gold wire 250~400μm.
- Chip microwave port without DC blocking capacitor.
- The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.